

## K. Memory (Design & Process Technology) 분과

2020년 2월 14일(금), 09:00-10:30 / Room G (스페이드 II+III, 6층)

### ■ [FG1-K] Emerging Memory II

좌장: 김윤 교수(서울시립대학교), 강명곤 교수(한국교통대학교)

FG1-K-1 09:00-09:30	<p>[초청]</p> <p><b>Memristor Crossbar Array with CMOS-compatible Etching-Down Fabrication Method and Its Applications</b></p> <p>Hyungjin Kim <i>Department of Electronic Engineering, Yeungnam University</i></p>
FG1-K-2 09:30-09:45	<p><b>Characteristics of a-IGZO Synaptic Transistor Having Extended Gate with Al<sub>2</sub>O<sub>3</sub> Gate Insulator by Low Temperature ALD</b></p> <p>Dongyeon Kang, Jun Tae Jang, Shinyoung Park, Dong Myong Kim, Sung-Jin Choi, and Dae Hwan Kim <i>School of Electrical Engineering, Kookmin University</i></p>
FG1-K-3 09:45-10:00	<p><b>The Influence of High Pressure Annealing on Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub> for Memory and Logic Applications</b></p> <p>Taeho Kim and Sanghun Jeon <i>School of Electrical Engineering, KAIST</i></p>
FG1-K-4 10:00-10:15	<p><b>Threshold Switching Phenomenon in 2D MXene Material for Electronic Synapse Applications</b></p> <p>Andrey S. Sokolov, Yu-Rim Jeon, Haider Abbas, and Changhwan Choi <i>Division of Materials Science and Engineering, Hanyang University</i></p>
FG1-K-5 10:15-10:30	<p><b>Combination-Encoding Content-Addressable Memory with High Content Density</b></p> <p>Guhyun Kim<sup>1</sup>, Cheol Seong Hwang<sup>1</sup>, and Doo Seok Jeong<sup>2</sup> <i><sup>1</sup>Seoul National University, <sup>2</sup>Hanyang University</i></p>